

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

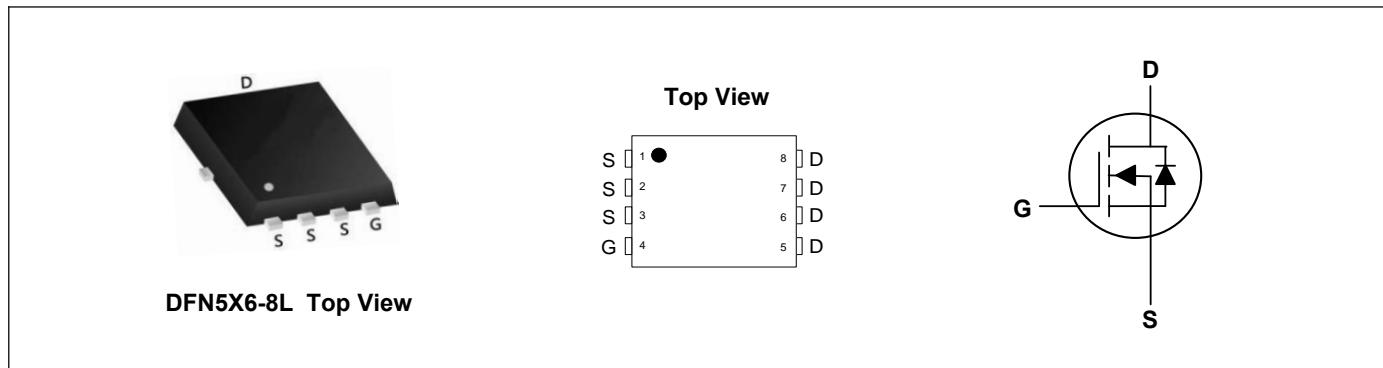
Product Summary



V_{DS}	120	V
I_D	18	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	40	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D @ T_c = 25^\circ\text{C}$	18	A
Continuous Drain Current ¹	$I_D @ T_c = 100^\circ\text{C}$	11	A
Pulsed Drain Current ²	I_{DM}	72	A
Single Pulse Avalanche Energy ³	E_{AS}	39	mJ
Total Power Dissipation ⁴	P_D	27	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	48	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	4.7	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	120	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=5\text{A}$	---	31	40	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D = 250\mu\text{A}$	2.0	---	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=96\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Total Gate Charge	Q_g	$V_{\text{DS}}=60\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=5\text{A}$	---	14	---	nC
Gate-Source Charge	Q_{gs}		---	5	---	
Gate-Drain Charge	Q_{gd}		---	3.2	---	
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DS}}=60\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=6\Omega$, $I_D=5\text{A}$	---	14	---	ns
Rise Time	T_r		---	17	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	22	---	
Fall Time	T_f		---	7	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=60\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	860	---	pF
Output Capacitance	C_{oss}		---	80	---	
Reverse Transfer Capacitance	C_{rss}		---	25	---	

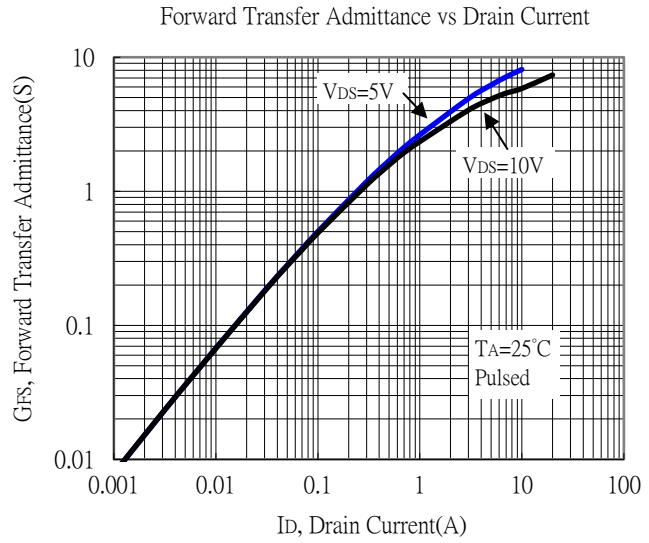
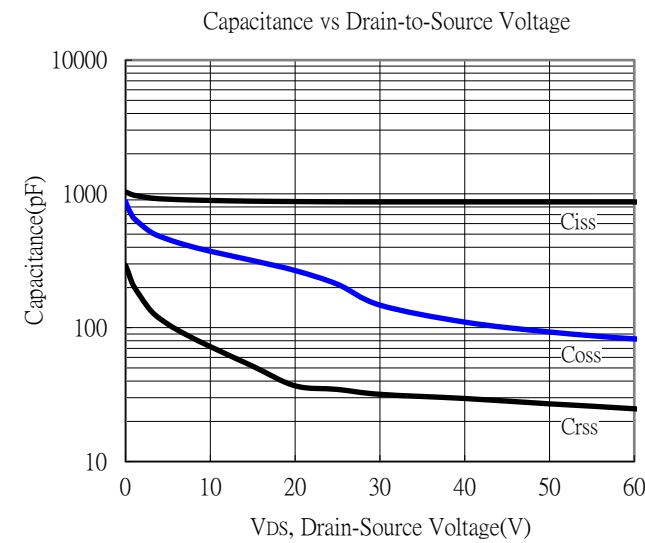
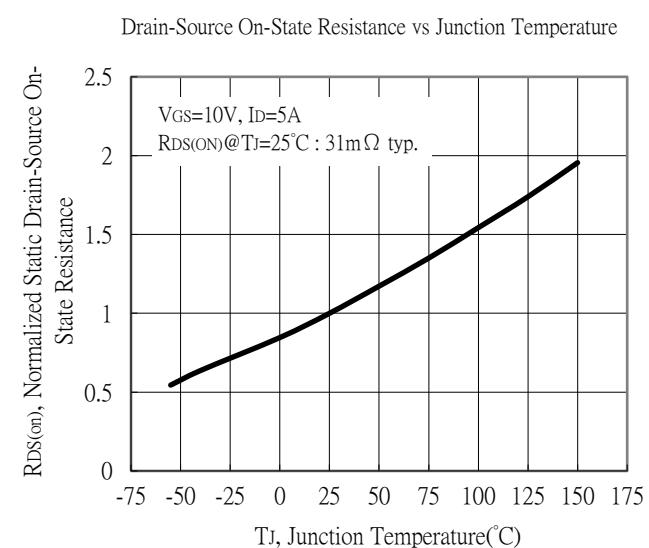
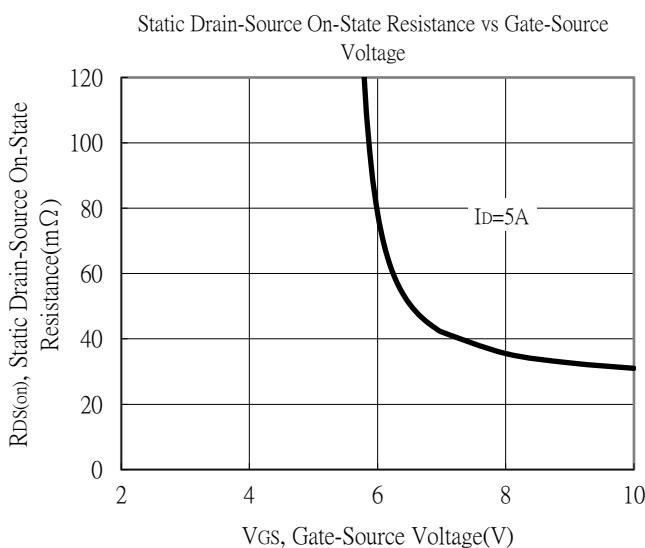
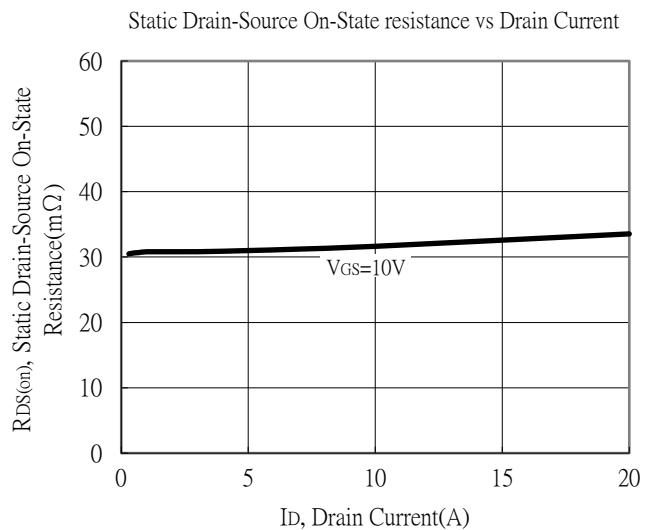
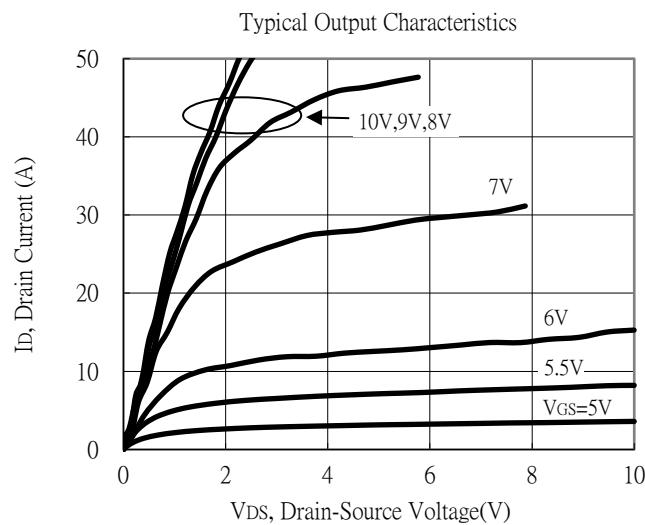
Drain-Source Diode Characteristics

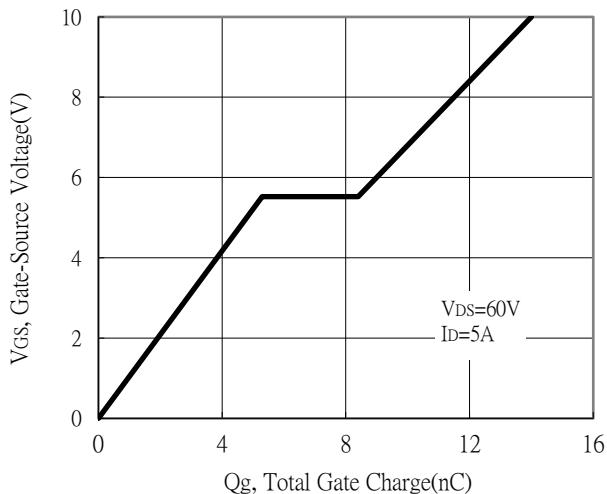
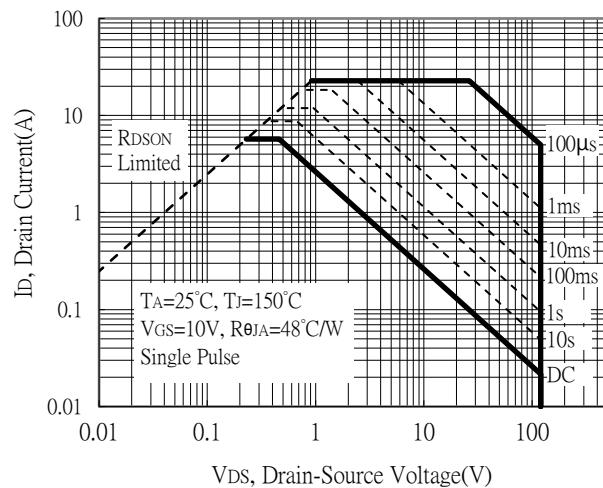
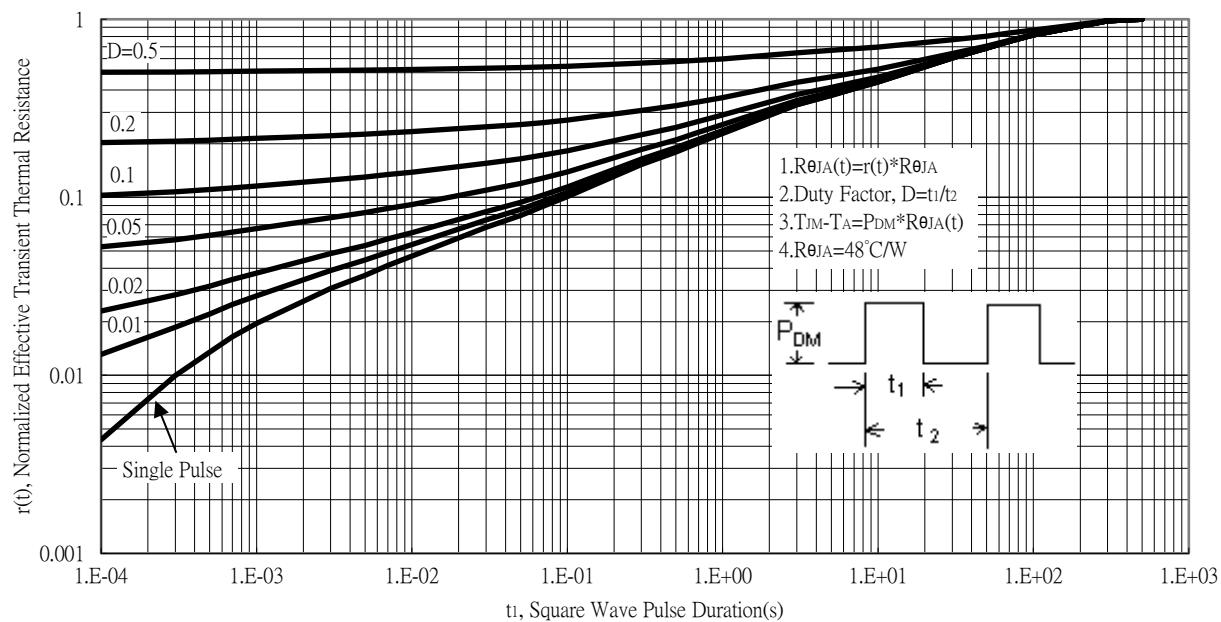
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=5\text{A}$, $T_J=25^\circ\text{C}$	---	0.8	1.2	V
Reverse Recovery Time	t_{rr}	$I_F=5\text{A}$, $V_R=0\text{V}$ $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	32	---	nS
Reverse Recovery Charge	Q_{rr}		---	48	---	nC

Note:

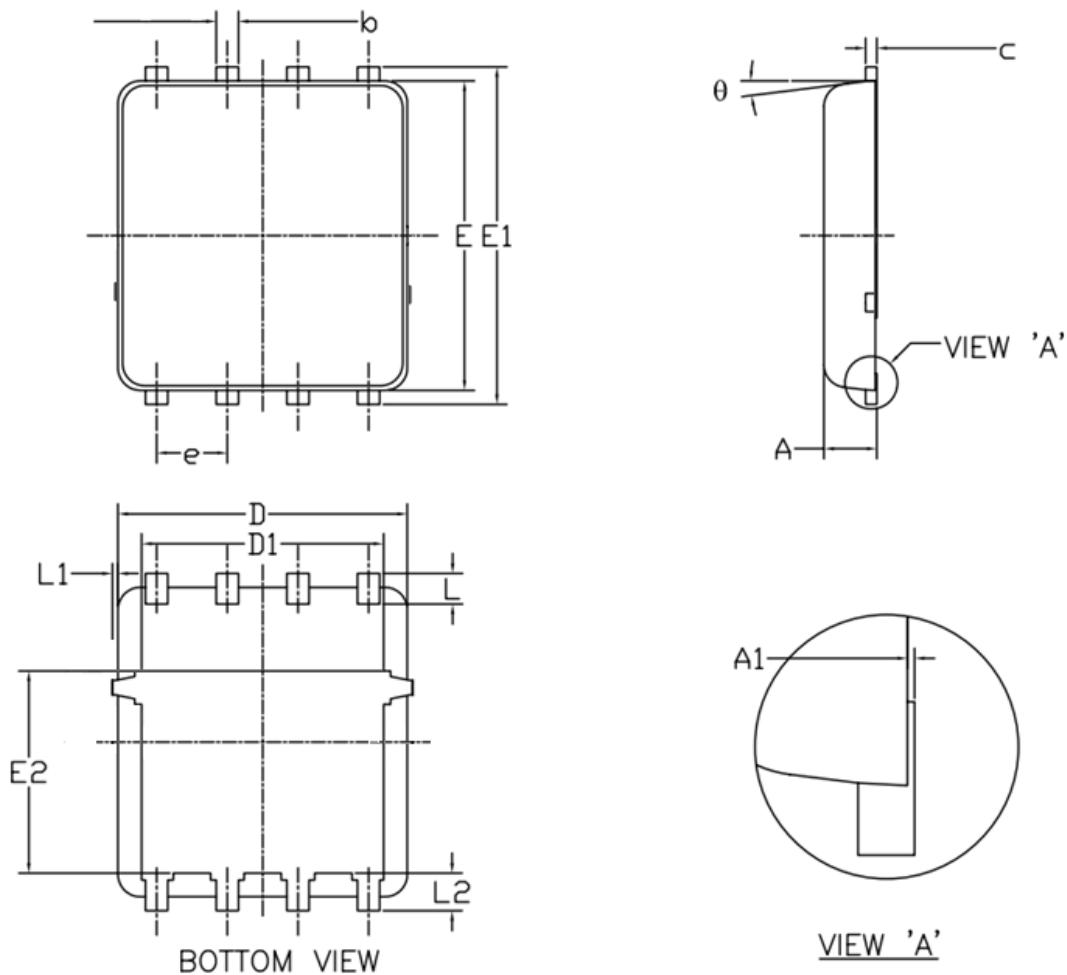
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=50\text{V}$, $I_D=5\text{A}$, $L=0.5\text{mH}$
4. The power dissipation is limited by 150°C junction temperature

Typical Characteristics



Gate Charge Characteristics

Maximum Safe Operating Area

Transient Thermal Response Curves


DFN5X6-8L Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.00	1.20	E1	5.90	6.10	6.35
A1	0.00	--	0.05	E2	3.38	3.58	3.92
b	0.30	0.40	0.51	e	1.27 BSC		
c	0.20	0.25	0.33	L	0.51	0.61	0.71
D	4.80	4.90	5.40	L1	--	--	0.15
D1	3.61	4.00	4.25	L2	0.41	0.51	0.61
E	5.65	5.80	6.06	θ	0°	--	12°